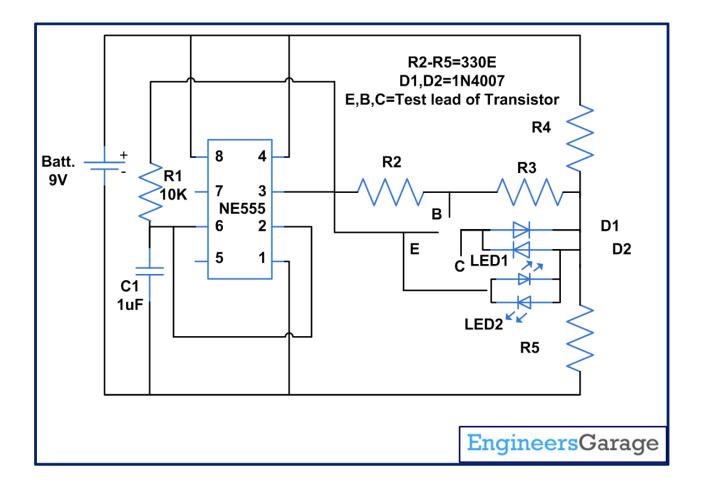
The Design Process, Part 2

Understanding what to do with the Bill of Materials

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Starting the library of parts is the next step. Each part on the Bill of Materials must be built and entered into the design. There are several pre-existing libraries that you can draw from as you wish, but I find it much easier to work with parts that I have built. Also, depending on the assembly process, parts may have to be built differently.

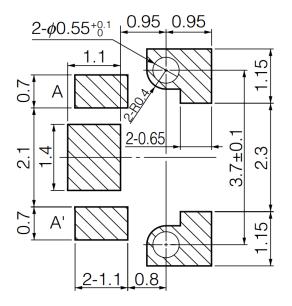
So, you've been handed a drawing that is covered with various symbols connected with lines. A part number and value may be drawn next to the symbols or maybe just a number corresponding to the same number on the parts list. Here is a sample.



Sometimes the engineer may also supply you with Data Sheets that tell you information about the part including what the PCB Footprint (the array of metal pads that the part will be soldered to) should look like. If you have to find your own data sheets, the easiest way is to do a web search for the part number. You may have to ask the engineer for clarification on several parts and on his connections...mistakes happen, don't be afraid to ask. Data Sheets may be just one page or multiple. In the case of complex integrated circuits, there may be

IPN G	eneral Purpose Ampl	ifier	•		
	s for use as a medium power amplifier and su n process 19.	witch requiring	collector current	s up to 500mA.	
	PN2222A MME	MMBT2222A		PZT2222A	
	ac TO-92 SOT-23 Maximum Ratings * Ta = 25°C unless	otherwise not	SOT	223 B C	E
	Parameter		Value	U	Units
Symbol	Parameter	Collector-Emitter Voltage			V
Symbol V _{CEO}			40		
			40		V
V _{CEO}	Collector-Emitter Voltage				v v
V _{CEO} V _{CBO}	Collector-Emitter Voltage Collector-Base Voltage		75 6.0 1.0		V A
V _{CEO} V _{CBO} V _{EBO} I _C T _{STG} This ratings a DTES:	Collector-Emitter Voltage Collector-Base Voltage Emitter-Base Voltage Collector Current Operating and Storage Junction Temperatu re limiting values above which the serviceability	lity of any sem	75 6.0 1.0 - 55 ~ 150 liconductor devic		V A °C
V _{CEO} V _{CBO} V _{CBO} I _C T _{STG} This ratings a DTES: These rating These rating These are st operations.	Collector-Emitter Voltage Collector-Base Voltage Emitter-Base Voltage Collector Current Operating and Storage Junction Temperatin are based on a maximum junction temperatu are based on a maximum junction temperatu and junits. The factory should be consulted haracteristics T _a = 25°C unless otherwite	lity of any sem ure of 150 deg on application	75 6.0 1.0 - 55 ~ 154 alconductor devic rees C.	e may be impai	V A •C red. cle
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V _{CEO} V _{CEO} V _{CEO} I _C T _{STG} his ratings a DTES : These rating These are st operations.	Collector-Emitter Voltage Collector-Base Voltage Emitter-Base Voltage Collector-Base Voltage Collector Current Operating and Storage Junction Temperatu there initing values above which the service which the service adv limits. The factory should be consulted haracteristics T _a = 25°C unless otherw Parameter Total Device Dissipation	lity of any sem ure of 150 deg on application ise noted PN2222A 625	75 6.0 1.0 55 ~ 150 ilconductor device rees C. s involving pulser Max. *MMBT2222A 350	d or low duty cy **PZT2222A 1,000	V A •C red. cle Units mW

hundreds of pages. Here are some examples of the information contained within data sheets (Note: in the example, PWB means Printed Wire Board, an older name for PCB).



When using the dimensions on data sheets, always check the numbers. Some are in metric (millimeters) and some are in English (inches), and occasionally in both, though I

PWB land pattern for reference

have found that they are not always converted correctly. If one dimension is given in parenthesis, that is not the controlling dimension.

Refer to The ANSI (American National Standards Institute) standard, <u>ANSI E32.2-1975</u>, on this web page for explanations of the schematic symbols and their reference designators.

Of course, we will go into all of this in greater detail later.

